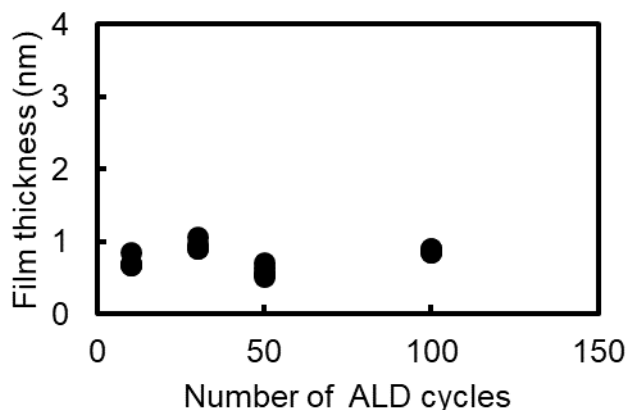
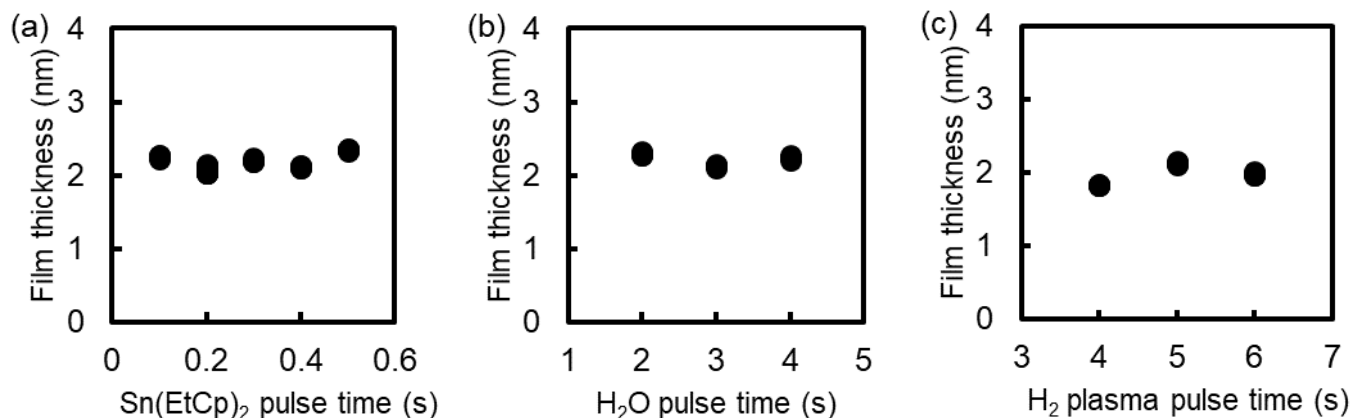


# Atomic Layer Deposition of SnO Film Using Liquid Sn(EtCp)<sub>2</sub> Precursor and Combinations of H<sub>2</sub>O and H<sub>2</sub> Plasma

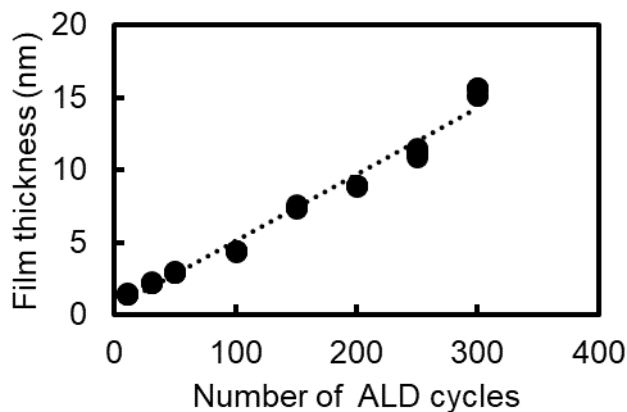
F. Mizutani, N. Takahashi, and T. Nabatame



SnO film thickness as a function of number of ALD cycles. The ALD process consisted of a Sn(EtCp)<sub>2</sub> pulse time of 0.2 s and an H<sub>2</sub>O pulse time of 3 s.



SnO film thickness as a function of (a) Sn(EtCp)<sub>2</sub> pulse time, (b) H<sub>2</sub>O pulse time, and (c) H<sub>2</sub> plasma pulse time for films deposited for 30 cycles. The Sn(EtCp)<sub>2</sub> pulse time, H<sub>2</sub>O pulse time, and H<sub>2</sub> plasma pulse time, except those that were varied, were 0.2, 3, and 5 s, respectively.



SnO film thickness as a function of number of ALD cycles. The ALD process consisted of a Sn(EtCp)<sub>2</sub> pulse time of 0.2 s, a H<sub>2</sub>O pulse time of 3 s, and a H<sub>2</sub> plasma pulse time of 5 s.